

## N-Channel Super Junction Power MOSFET III

### General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

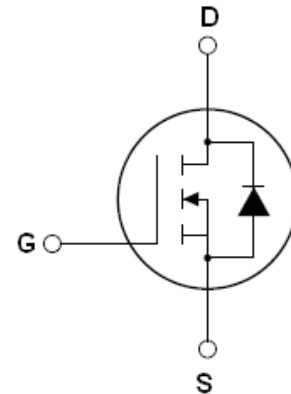
### Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- OHS compliant

### Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

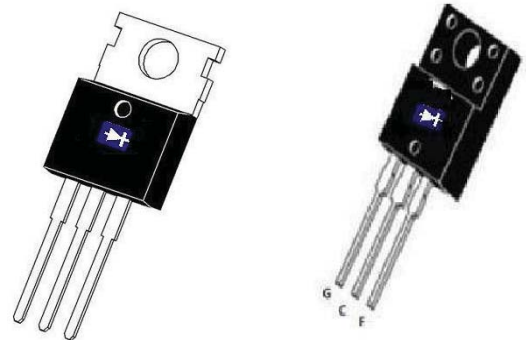
$V_{DS}$	800	V
$R_{DS(ON) MAX}$	420	m $\Omega$
$I_D$	11	A



**Schematic diagram**

### Package Marking And Ordering Information

Device	Device Package	Marking
RM11N800T2	TO-220	11N800
RM11N800T1	TO-220F	11N800



**TO-220**

**TO-220F**

**Table 1. Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )**

Parameter	Symbol	RM11N800T2	RM11N800T1	Unit
Drain-Source Voltage ( $V_{GS}=0V$ )	$V_{DS}$	800		V
Gate-Source Voltage ( $V_{DS}=0V$ ), AC ( $f>1$ Hz)	$V_{GS}$	$\pm 30$		V
Continuous Drain Current at $T_C=25^\circ\text{C}$	$I_{D(DC)}$	11	11*	A
Continuous Drain Current at $T_C=100^\circ\text{C}$	$I_{D(DC)}$	8.5	8.5*	A
Pulsed drain current <sup>(Note 1)</sup>	$I_{DM(pluse)}$	44	44*	A
Maximum Power Dissipation( $T_C=25^\circ\text{C}$ )	$P_D$	188	33.8	W
$R_{\theta JC}$ Derate above $25^\circ\text{C}$		1.5	0.27	W/ $^\circ\text{C}$
Single pulse avalanche energy <sup>(Note 2)</sup>	$E_{AS}$	144		mJ
Avalanche current <sup>(Note 1)</sup>	$I_{AR}$	6		A
Repetitive Avalanche energy, $t_{AR}$ limited by $T_{Jmax}$ <sup>(Note 1)</sup>	$E_{AR}$	0.7		mJ

Parameter	Symbol	RM11N800T2	RM11N800T1	Unit
Drain Source voltage slope, $V_{DS} \leq 480V$ ,	dv/dt	50		V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	15		V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55...+150		°C

\* limited by maximum junction temperature

**Table 2. Thermal Characteristic**

Parameter	Symbol	RM11N800T2	RM11N800T1	Unit
Thermal Resistance, Junction-to-Case (Maximum)	$R_{thJC}$	0.66	3.69	°C/W
Thermal Resistance, Junction-to-Ambient (Maximum)	$R_{thJA}$	62.5	80	°C/W

**Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>On/off states</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	800			V
Zero Gate Voltage Drain Current( $T_C=25^\circ C$ )	$I_{DSS}$	$V_{DS}=800V, V_{GS}=0V$		0.05	1	$\mu A$
Zero Gate Voltage Drain Current( $T_C=125^\circ C$ )	$I_{DSS}$	$V_{DS}=800V, V_{GS}=0V$			100	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3	3.5	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5.5A$		350	420	m $\Omega$
<b>Dynamic Characteristics</b>						
Forward Transconductance	$g_{FS}$	$V_{DS} = 20V, I_D = 5.5A$		7		S
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$		2600		PF
Output Capacitance	$C_{oss}$			95		PF
Reverse Transfer Capacitance	$C_{rss}$			7		PF
Total Gate Charge	$Q_g$	$V_{DS}=640V, I_D=11A,$ $V_{GS}=10V$		48		nC
Gate-Source Charge	$Q_{gs}$			17		nC
Gate-Drain Charge	$Q_{gd}$			14		nC
<b>Switching times</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=480V, I_D=5.5A,$ $R_G=4\Omega, V_{GS}=10V$		12		nS
Turn-on Rise Time	$t_r$			7		nS
Turn-Off Delay Time	$t_{d(off)}$			62		nS
Turn-Off Fall Time	$t_f$			5		nS
<b>Source- Drain Diode Characteristics</b>						
Source-drain current(Body Diode)	$I_{SD}$	$T_C=25^\circ C$			11	A
Pulsed Source-drain current(Body Diode)	$I_{SDM}$				44	A
Forward on voltage	$V_{SD}$	$T_J=25^\circ C, I_{SD}=11A, V_{GS}=0V$		0.9	1.3	V
Reverse Recovery Time	$t_{rr}$	$T_J=25^\circ C, I_F=11A, di/dt=100A/\mu s$		290		nS
Reverse Recovery Charge	$Q_{rr}$			2.2		$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$			15		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.  $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

# RATING AND CHARACTERISTICS CURVES (RM11N800T1, RM11N800T2)

Figure1. Safe operating area for TO-220

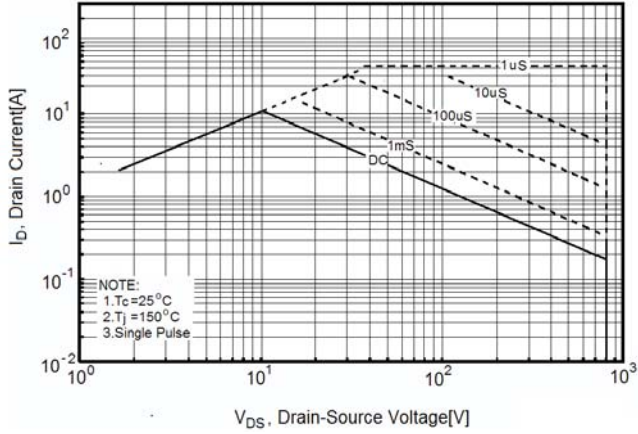


Figure2. Safe operating area for TO-220F

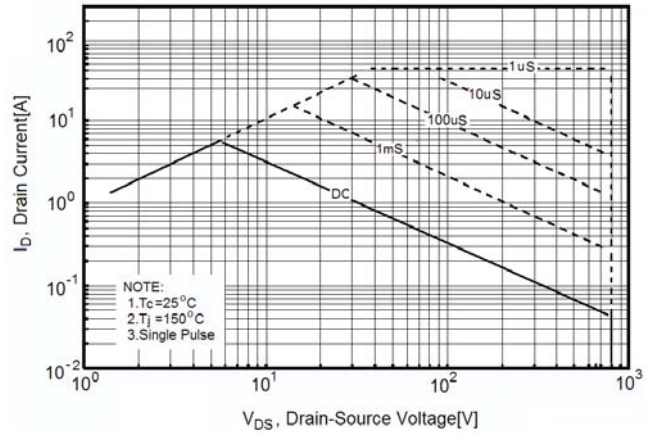


Figure3. Source-Drain Diode Forward Voltage

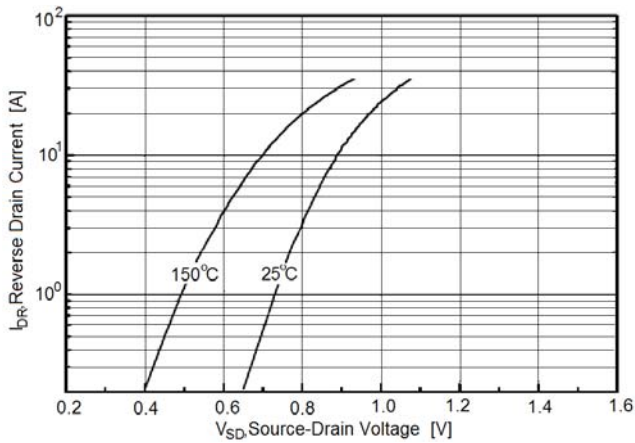


Figure4. Output characteristics

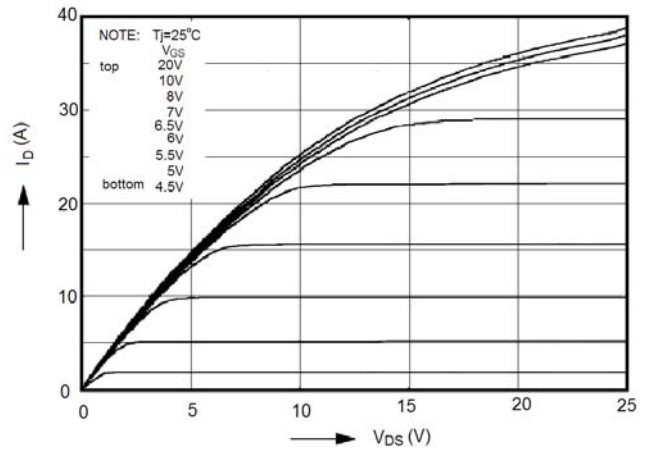


Figure5. Transfer characteristics

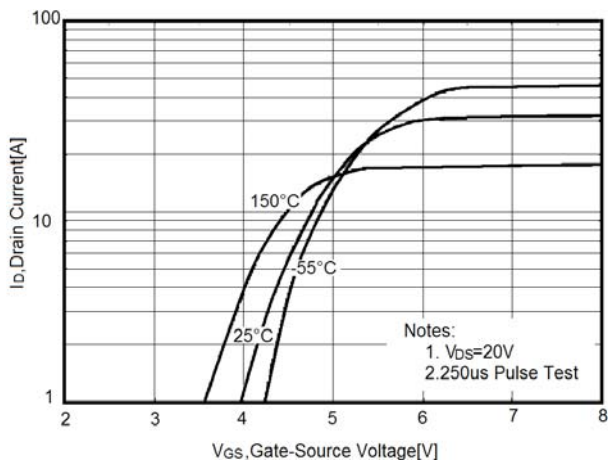
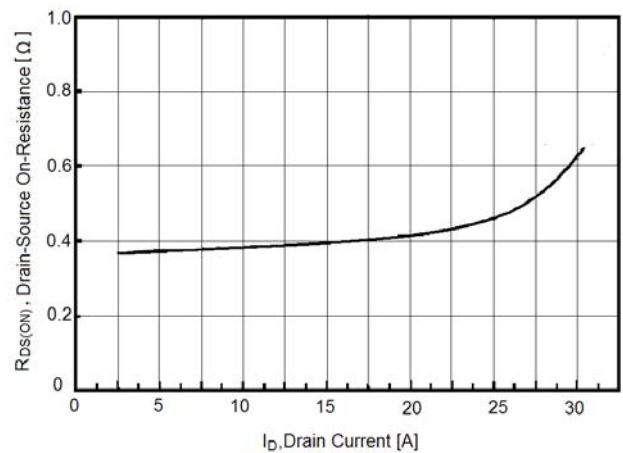


Figure6. Static drain-source on resistance



# RATING AND CHARACTERISTICS CURVES (RM11N800T1, RM11N800T2)

Figure7.  $R_{DS(ON)}$  vs Junction Temperature

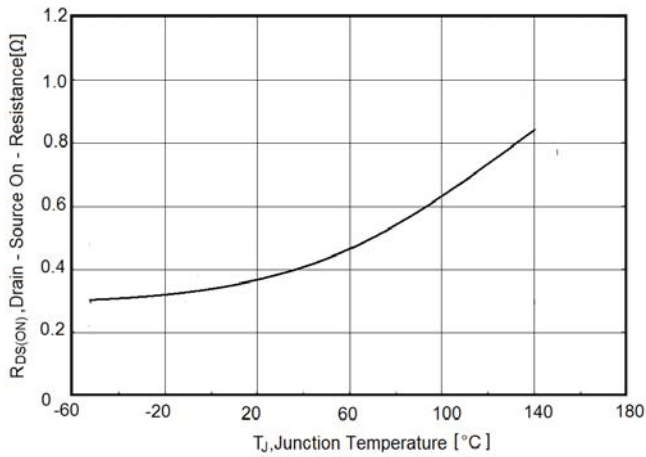


Figure8.  $BV_{DSS}$  vs Junction Temperature

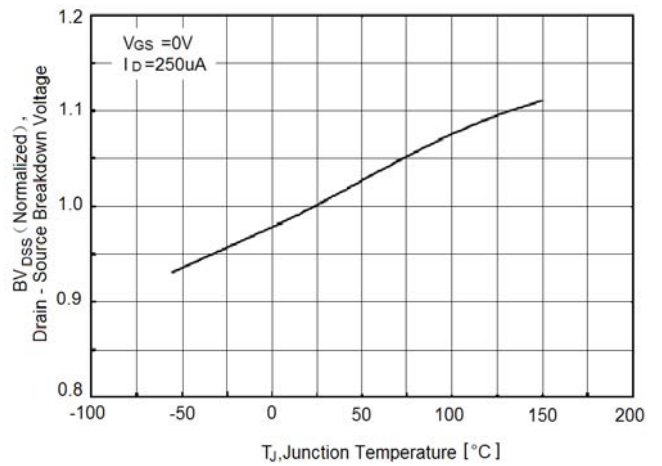


Figure9. Maximum  $I_D$  vs Junction Temperature

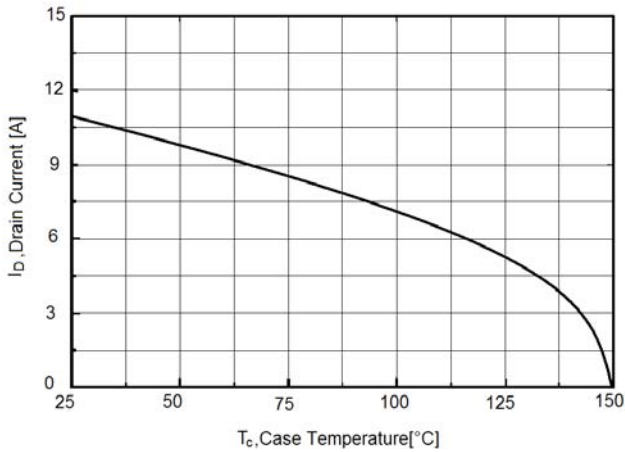


Figure10. Transient Thermal Impedance for TO-220

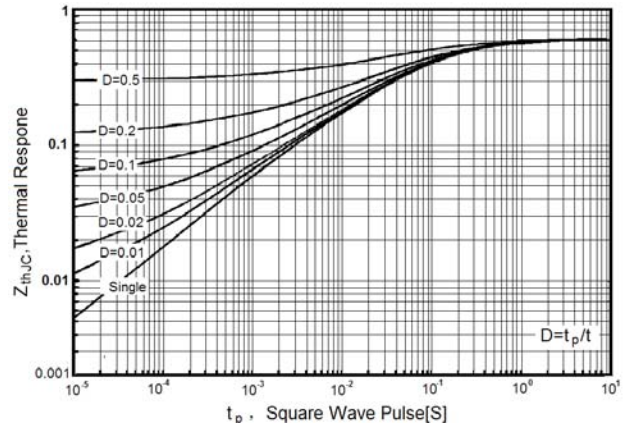
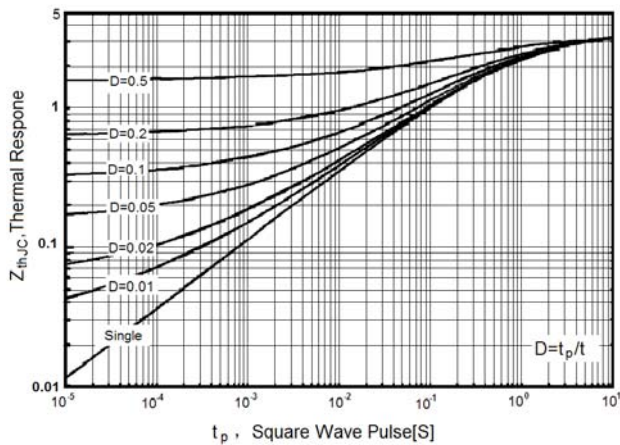
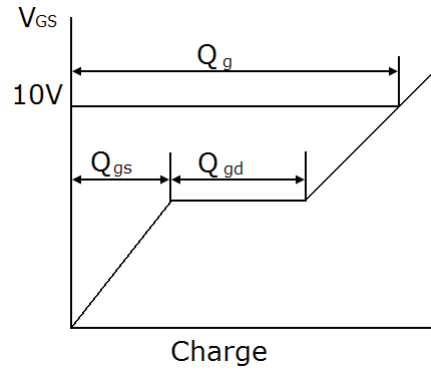
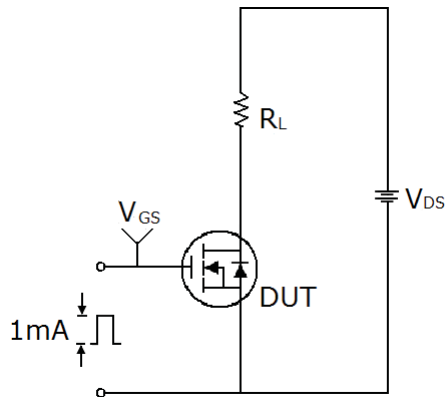


Figure11. Transient Thermal Impedance for TO-220F

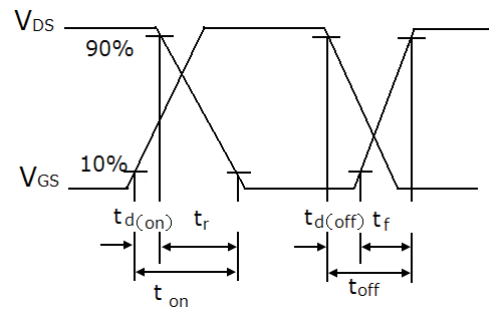
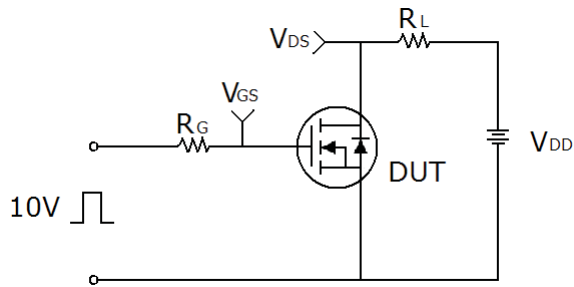


# Test circuit

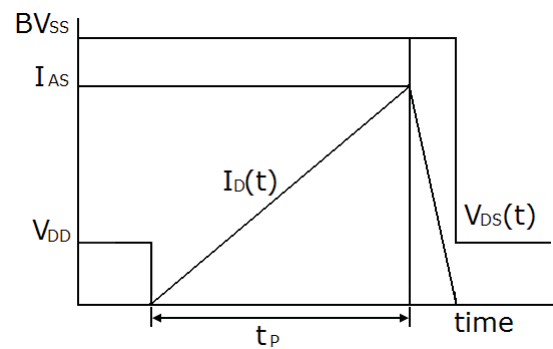
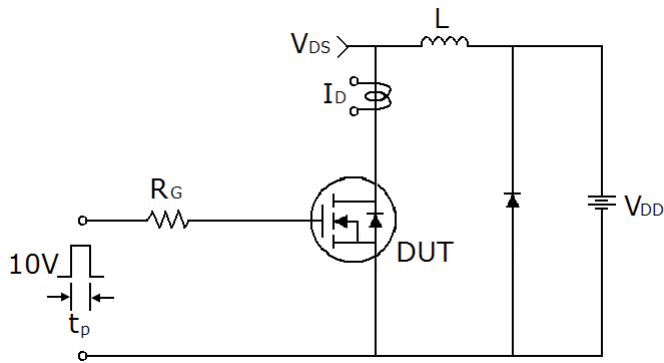
## 1) Gate charge test circuit & Waveform



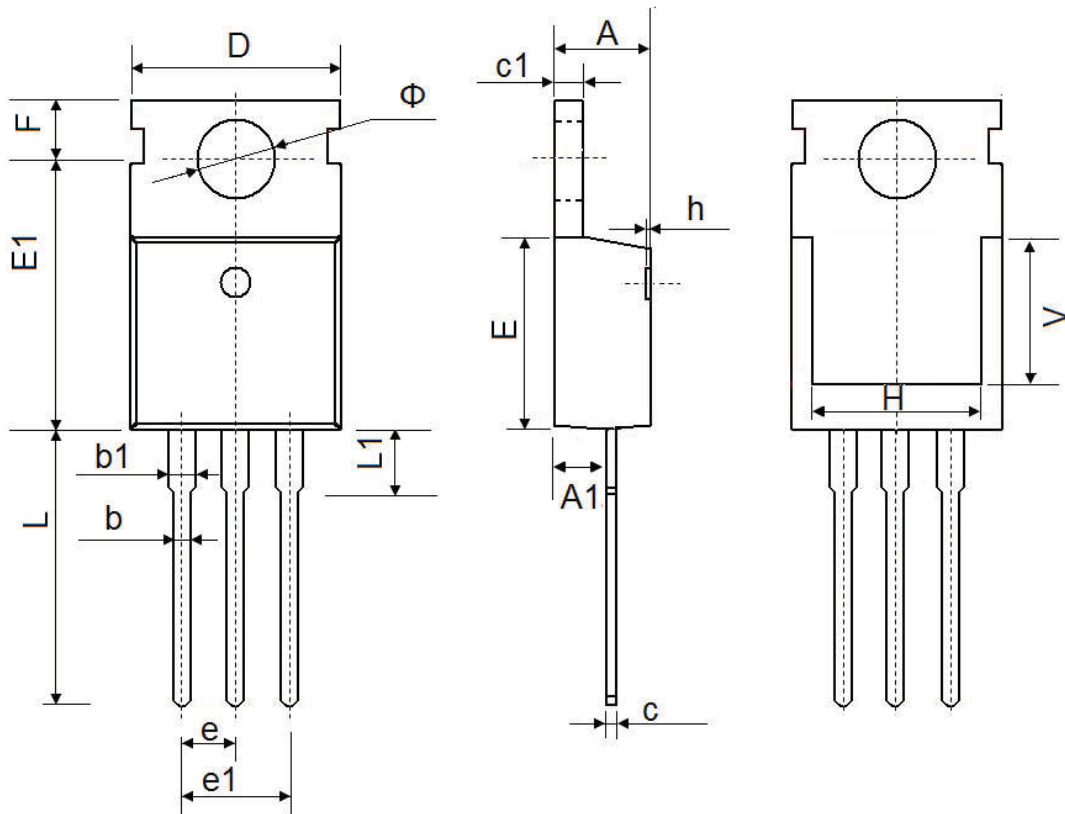
## 2) Switch Time Test Circuit:



## 3) Unclamped Inductive Switching Test Circuit & Waveforms

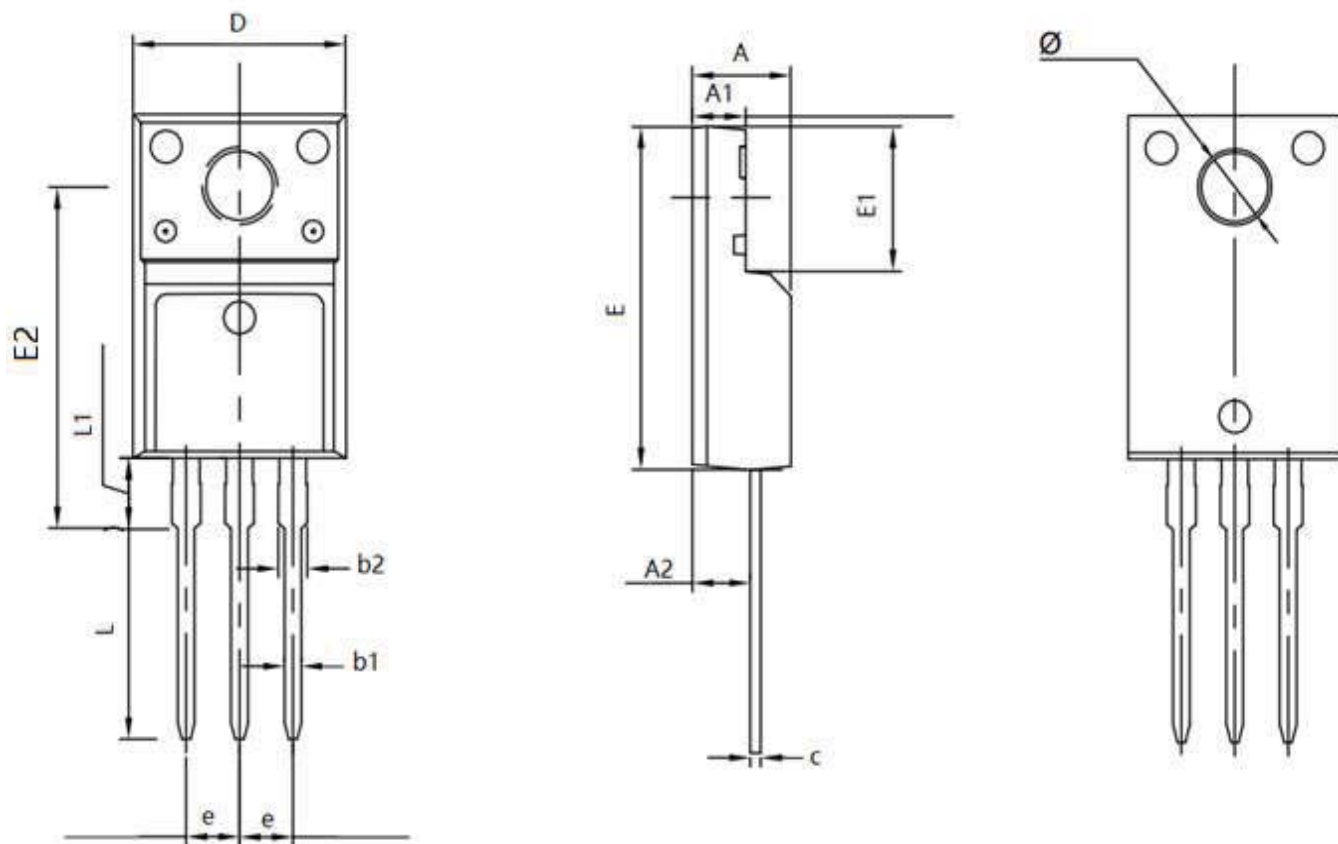


# TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
$\Phi$	3.400	3.800	0.134	0.150

# TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.500	4.900	0.177	0.193
A1	2.340	2.740	0.092	0.108
A2	2.560	2.960	0.101	0.117
b1	0.700	0.900	0.028	0.035
b2	1.180	1.580	0.046	0.062
c	0.400	0.600	0.016	0.024
D	9.960	10.360	0.392	0.408
E	15.670	15.970	0.617	0.629
E1	6.500	6.900	0.256	0.272
E2	15.500	16.100	0.610	0.634
e	2.540 TYP		0.100 TYP	
$\phi$	3.080	3.280	0.121	0.129
L	12.640	13.240	0.498	0.521
L1	3.030	3.430	0.119	0.135

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